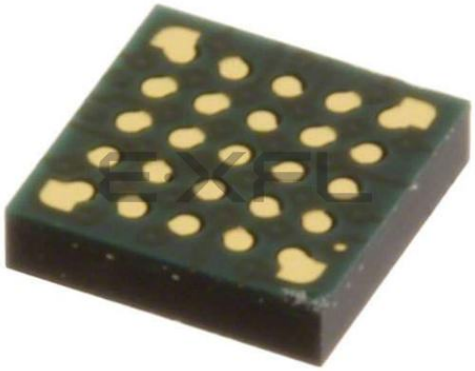
Renesas Electronics America Inc - R5F1058AALA#U0 Datasheet



Welcome to E-XFL.COM

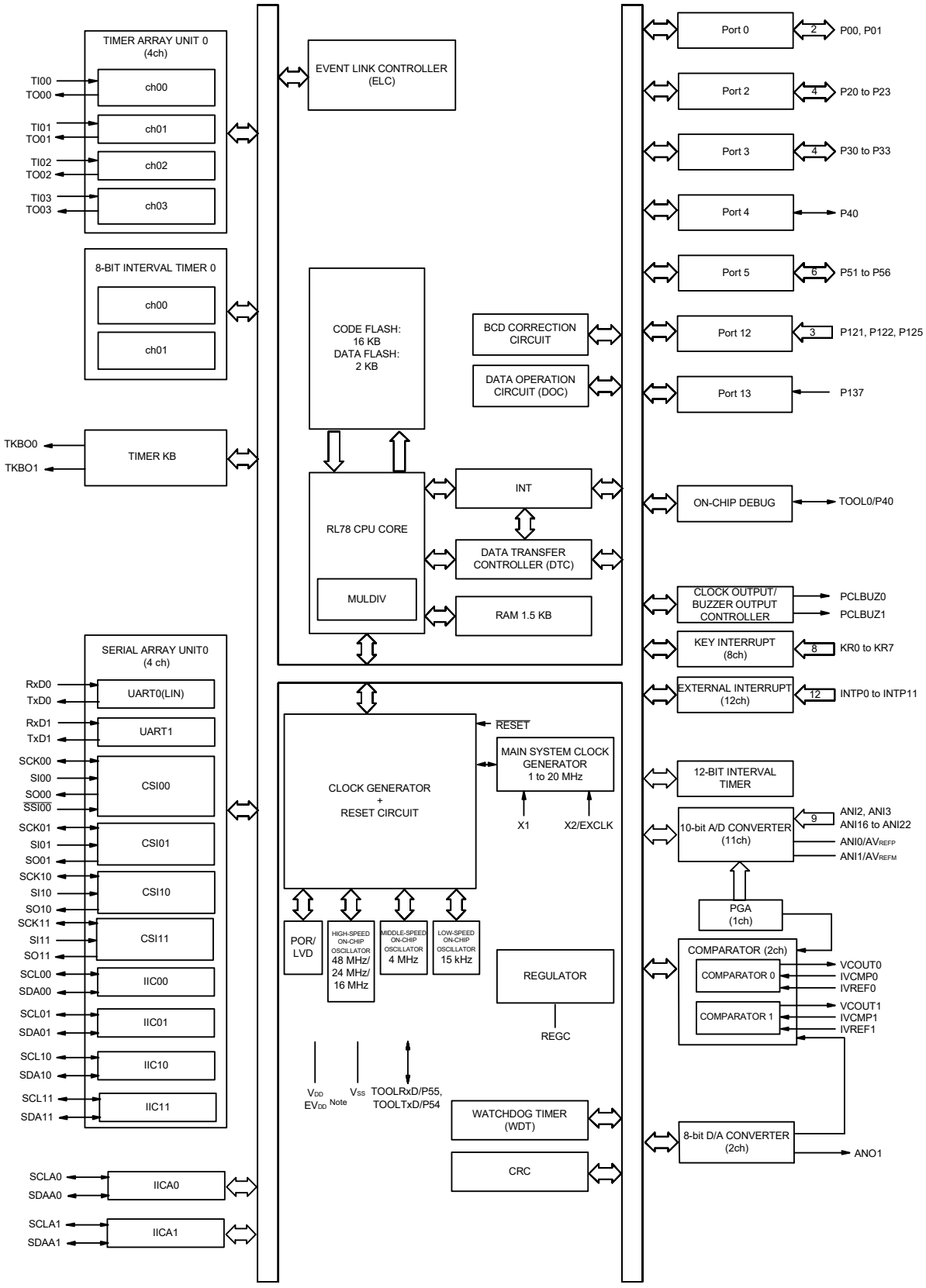
What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, UART/USART
Peripherals	LVD, POR, WDT
Number of I/O	21
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 11x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	25-WFLGA
Supplier Device Package	25-LGA (3x3)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1058aala-u0

<R> 1.5.4 24-pin, 25-pin products



Note 25-pin products

(2/2)

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	I_{OH1}	Per pin		-40	mA
		Total of all pins -170 mA	P00, P01, P40	-70	mA
			P30 to P33, P51 to P56	-100	mA
	I_{OH2}	Per pin	P20 to P23	-0.5	mA
		Total of all pins		-2	mA
Output current, low	I_{OL1}	Per pin		40	mA
		Total of all pins 170 mA	P00, P01, P40	70	mA
			P30 to P33, P51 to P56	100	mA
	I_{OL2}	Per pin	P20 to P23	1	mA
		Total of all pins		4	mA
Operating ambient temperature	T_A	In normal operation mode		-40 to +85	°C
		In flash memory programming mode			
Storage temperature	T_{stg}			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(4/4)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD3} Note 2	STOP mode Note 3	T_A = -40°C		0.19	0.51	μA
			T_A = +25°C		0.25	0.51	
			T_A = +50°C		0.28	1.10	
			T_A = +70°C		0.38	1.90	
			T_A = +85°C		0.60	3.30	

Note 1. Total current flowing into V_{DD} and EV_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The MAX values include the peripheral operating current. However, these values do not include the current flowing into the A/D converter, comparator, Programmable gain amplifier, LVD circuit, I/O ports, and on-chip pull-up/pull-down resistors, and the current flowing during data flash rewrite.

Note 2. The values do not include the current flowing into the 12-bit interval timer and watchdog timer.

Note 3. For the setting of the current values when operating the subsystem clock in STOP mode, see the current values when operating the subsystem clock in HALT mode.

Peripheral Functions (Common to all products)

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I_{FIL} Note 1				0.20		μA
12-bit interval timer operating current	I_{TMKA} Notes 1, 3, 4	f_{IL} = 15 kHz f_{MAIN} stopped (per unit)			0.02		μA
8-bit interval timer operating current Notes 1, 9	I_{TMT}	f_{IL} = 15 kHz f_{MAIN} stopped (per unit)	8-bit counter mode × 2-channel operation		0.04		μA
			16-bit counter mode operation		0.03		μA
Watchdog timer operating current	I_{WDT} Notes 1, 3, 5	f_{IL} = 15 kHz f_{MAIN} stopped (per unit)			0.22		μA
A/D converter operating current	I_{ADC} Notes 1, 6	During maximum-speed conversion	Normal mode, AV_{VREFP} = V_{DD} = 5.0 V		1.3	1.7	mA
			Low voltage mode, AV_{VREFP} = V_{DD} = 3.0 V		0.5	0.7	mA
Internal reference voltage (1.45 V) current Notes 1, 10	I_{ADREF}				85.0		μA
Temperature sensor operating current	I_{TMPS} Note 1				85.0		μA
D/A converter operating current	I_{DAC} Note 1	Per channel				1.5	mA
PGA operating current	I_{PGA} Notes 1, 2				480	700	μA
Comparator operating current	I_{CMP} Note 8	V_{DD} = 5.0 V, Regulator output voltage = 2.1 V	Comparator high-speed mode Window mode		12.5		μA
			Comparator low-speed mode Window mode		3.0		
			Comparator high-speed mode Standard mode		6.5		
			Comparator low-speed mode Standard mode		1.9		
		V_{DD} = 5.0 V, Regulator output voltage = 1.8 V	Comparator high-speed mode Window mode		8.0		
			Comparator low-speed mode Window mode		2.2		
			Comparator high-speed mode Standard mode		4.0		
			Comparator low-speed mode Standard mode		1.3		
LVD operating current	I_{LVD} Notes 1, 7				0.10		μA
Self-programming operating current	IFSP Notes 1, 12				2.0	12.20	mA
BGO current	IBGO Notes 1, 11				2.0	12.20	mA
SNOOZE operating current	ISNOZ Note 1	ADC operation f_{IH} = 24 MHz, AVREFP = V_{DD} = 3.0 V	Mode transition Note 13		0.50	0.60	mA
			The A/D conversion operations are performed		1.20	1.44	mA
		CSI/UART operation f_{IH} = 24 MHz			0.70	0.84	mA
	ISNOZM Note 1	ADC operation f_{IM} = 4 MHz, AVREFP = V_{DD} = 3.0 V	Mode transition Note 13		0.05	0.08	mA
			The A/D conversion operations are performed		0.67	0.78	mA
		CSI operation, f_{IM} = 4 MHz			0.06	0.08	mA

(**Notes** and **Remarks** are listed on the next page.)

2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

When P01, P30, P31 and P54 are used as TxDq pins

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1, 2		2.7 V ≤ EV_{DD} ≤ 5.5V		f_{MCK}/6		f_{MCK}/6		f_{MCK}/6		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.1		0.6	Mbps
		1.8 V ≤ EV_{DD} ≤ 5.5 V		f_{MCK}/6		f_{MCK}/6		f_{MCK}/6		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.1		0.6	Mbps
		1.7 V ≤ EV_{DD} ≤ 5.5 V		f_{MCK}/6		f_{MCK}/6		f_{MCK}/6		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.1		0.6	Mbps
		1.6 V ≤ EV_{DD} ≤ 5.5 V	—			f_{MCK}/6		f_{MCK}/6		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3	—			1.3		0.1		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. Following conditions must be satisfied on low level interface of EV_{DD} < V_{DD}.
2.4 V ≤ EV_{DD} ≤ 2.7 V: MAX.2.6 Mbps
1.8 V ≤ EV_{DD} ≤ 2.4 V: MAX.1.3 Mbps
1.6 V ≤ EV_{DD} ≤ 1.8 V: MAX.0.6 Mbps

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ EV_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ EV_{DD} ≤ 5.5 V)
LS (low-speed main) mode: 8 MHz (1.8 V ≤ EV_{DD} ≤ 5.5 V)
LP (low-power main) mode: 1 MHz (1.8 V ≤ EV_{DD} ≤ 5.5 V)
LV (low-voltage main) mode: 4 MHz (1.6 V ≤ EV_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

(6) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (UART mode) (dedicated baud rate generator output)

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		reception	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.1		0.6	Mbps
			2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.1		0.6	Mbps
			1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		f_{MCK}/6 Notes 1, 2, 4		f_{MCK}/6 Notes 1, 2		f_{MCK}/6 Notes 1, 2		f_{MCK}/6 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.1		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4,800 bps only.

Note 2. Use it with EV_{DD} ≥ Vb.

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)
LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)
LP (low-power main) mode: 1 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)
LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

Note 4. The following conditions are required for low voltage interface when EV_{DD} < V_{DD}
2.4 V ≤ EV_{DD} < 2.7 V: MAX. 2.6 Mbps
1.8 V ≤ EV_{DD} < 2.4 V: MAX. 1.3 Mbps

Caution **Select the TTL input buffer for the RxDq pin and the N-ch open drain output (EV_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

Remark 1. V_b[V]: Communication line voltage

Remark 2. q: UART number (q = 0 and 1), g: PIM and POM number (g = 0, 2, 3, 5 and 12)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))

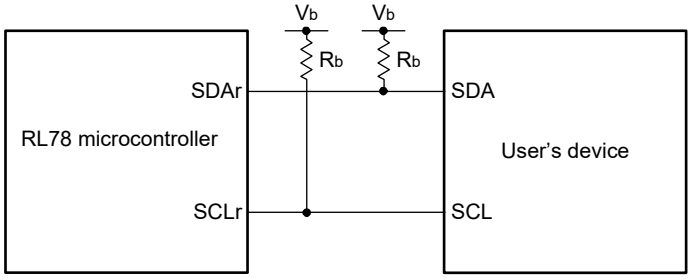
Note 1. The value must be equal to or less than f_{MCK}/4.

Note 2. Use it with $EV_{DD} \geq V_b$.

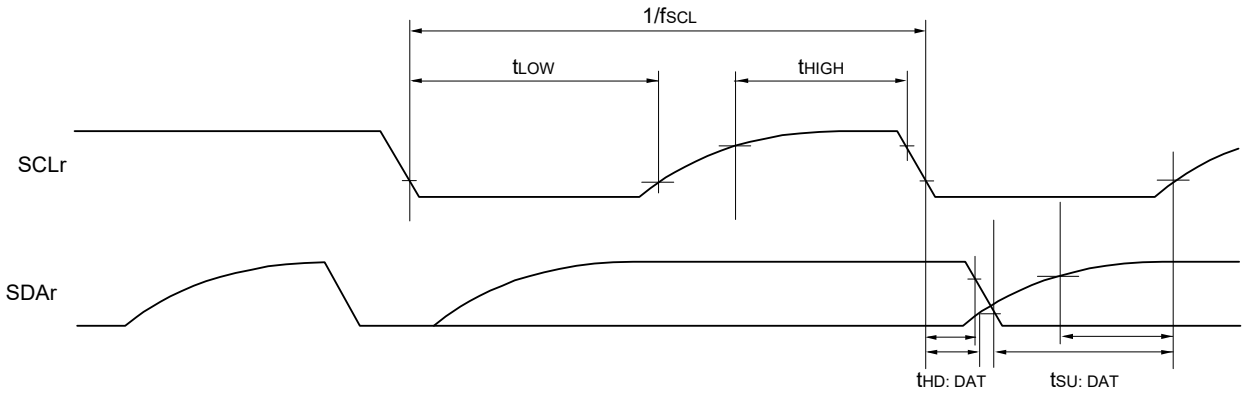
Note 3. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (EV_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (EV_{DD} tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 01, 10 and 11), g: PIM, POM number (g = 0, 3 and 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3), mn = 00 to 03)

2.5.2 Serial interface IICA

(1) I^2C standard mode

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LP (Low-power main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Standard mode: f_{CLK} ≥ 1 MHz	2.7 V ≤ EV_{DD} ≤ 5.5 V	0	100	0	100	0	100	0	100	kHz
			1.8 V ≤ EV_{DD} ≤ 5.5 V	0	100	0	100	0	100	0	100	kHz
			1.7 V ≤ EV_{DD} ≤ 5.5 V	0	100	0	100	0	100	0	100	kHz
			1.6 V ≤ EV_{DD} ≤ 5.5 V	—		0	100	0	100	0	100	kHz
Setup time of restart condition	$t_{SU: STA}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		4.7		µs
		1.8 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		4.7		µs
		1.7 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		4.7		µs
		1.6 V ≤ EV_{DD} ≤ 5.5 V		—		4.7		4.7		4.7		µs
Hold time Note 1	$t_{HD: STA}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		4.0		µs
		1.8 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		4.0		µs
		1.7 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		4.0		µs
		1.6 V ≤ EV_{DD} ≤ 5.5 V		—		4.0		4.0		4.0		µs
Hold time when SCLA0 = "L"	t_{LOW}	2.7 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		4.7		µs
		1.8 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		4.7		µs
		1.7 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		4.7		µs
		1.6 V ≤ EV_{DD} ≤ 5.5 V		—		4.7		4.7		4.7		µs
Hold time when SCLA0 = "H"	t_{HIGH}	2.7 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		4.0		µs
		1.8 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		4.0		µs
		1.7 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		4.0		µs
		1.6 V ≤ EV_{DD} ≤ 5.5 V		—		4.0		4.0		4.0		µs
Data setup time (reception)	$t_{SU: DAT}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		250		250		250		250		ns
		1.8 V ≤ EV_{DD} ≤ 5.5 V		250		250		250		250		ns
		1.7 V ≤ EV_{DD} ≤ 5.5 V		250		250		250		250		ns
		1.6 V ≤ EV_{DD} ≤ 5.5 V		—		250		250		250		ns
Data hold time (transmission) Note 2	$t_{HD: DAT}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0	3.45	0	3.45	0	3.45	0	3.45	µs
		1.8 V ≤ EV_{DD} ≤ 5.5 V		0	3.45	0	3.45	0	3.45	0	3.45	µs
		1.7 V ≤ EV_{DD} ≤ 5.5 V		0	3.45	0	3.45	0	3.45	0	3.45	µs
		1.6 V ≤ EV_{DD} ≤ 5.5 V		—		0	3.45	0	3.45	0	3.45	µs
Setup time of stop condition	$t_{SU: STO}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		4.0		µs
		1.8 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		4.0		µs
		1.7 V ≤ EV_{DD} ≤ 5.5 V		4.0		4.0		4.0		4.0		µs
		1.6 V ≤ EV_{DD} ≤ 5.5 V		—		4.0		4.0		4.0		µs
Bus-free time	t_{BUF}	2.7 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		4.7		µs
		1.8 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		4.7		µs
		1.7 V ≤ EV_{DD} ≤ 5.5 V		4.7		4.7		4.7		4.7		µs
		1.6 V ≤ EV_{DD} ≤ 5.5 V		—		4.7		4.7		4.7		µs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of $t_{HD: DAT}$ is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V		1.2	±7.0	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V Note 3		1.2	±10.5	LSB
Conversion time	tCONV	10-bit resolution Target pin: ANI0 to ANI3, ANI16 to ANI22	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V_{DD} ≤ 5.5 V	57		95	μs
		10-bit resolution Target pin: internal reference voltage, and temperature sensor output voltage	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	EZS	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V_{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V_{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±4.0	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V Note 3			±6.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V Note 3			±2.5	LSB
Analog input voltage	VAIN	ANI0 to ANI3		0		V_{DD}	V
		ANI16 to ANI22		0		EV_{DD}	V
		Internal reference voltage (1.8 V ≤ V_{DD} ≤ 5.5 V)		V_{BGR} Note 4			V
		Temperature sensor output voltage (1.8 V ≤ V_{DD} ≤ 5.5 V)		V_{TMPS25} Note 4			V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

Note 4. Refer to **2.6.2 Temperature sensor characteristics/internal reference voltage characteristic**.

2.6.2 Temperature sensor characteristics/internal reference voltage characteristic

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, T_A = +25°C		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	t_{AMP}	2.4 V ≤ V_{DD} ≤ 5.5 V	5			μs
		1.8 V ≤ V_{DD} < 2.4 V	10			μs

2.6.3 D/A converter characteristics

(T_A = -40 to +85°C, 1.6 V ≤ EV_{SS} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

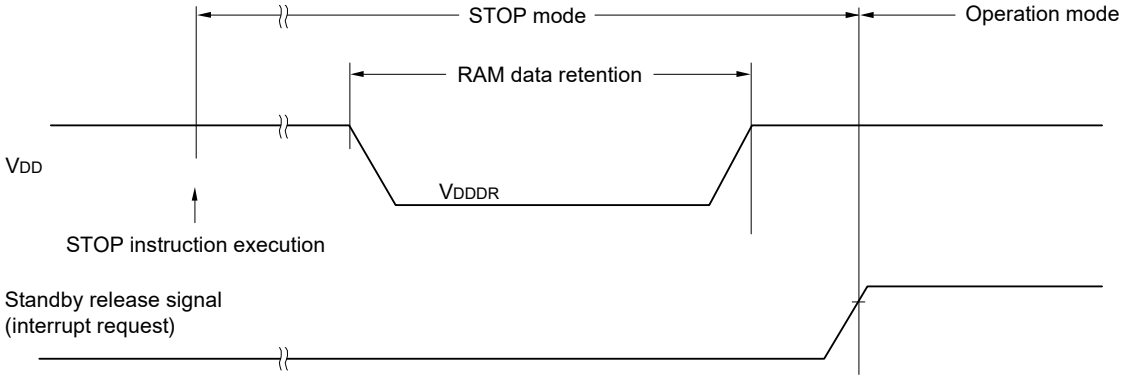
Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 MΩ	1.8 V ≤ V_{DD} ≤ 5.5 V			±2.5	LSB
		Rload = 8 MΩ	1.8 V ≤ V_{DD} ≤ 5.5 V			±2.5	LSB
Settling time	t_{SET}	Cload = 20 pF	2.7 V ≤ V_{DD} ≤ 5.5 V			3	μs
			1.6 V ≤ V_{DD} < 2.7 V			6	μs

2.7 RAM Data Retention Characteristics

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46 Note		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



2.8 Flash Memory Programming Characteristics

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
System clock frequency	f_{CLK}			1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	C_{erwr}	Retained for 20 years	T_A = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year	T_A = 25°C		1,000,000		
		Retained for 5 years	T_A = 85°C	100,000			
		Retained for 20 years	T_A = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

2.10 Timing of Entry to Flash Memory Programming Modes

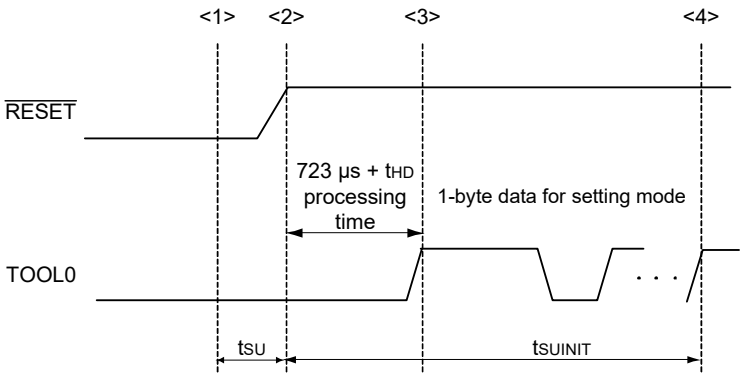
(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified Note 1	t_{SUINIT}	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends Note 1	t_{SU}	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory) Notes 1, 2	t_{HD}	POR and LVD reset must end before the external reset ends.	1			ms

Note 1. Deassertion of the POR and LVD reset signals must precede deassertion of the pin reset signal.

Note 2. This excludes the flash firmware processing time (723 μs).

<R>



<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the external reset ends).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

t_{SU}: How long from when the TOOL0 pin is placed at the low level until a pin reset ends

t_{HD}: How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)

3. ELECTRICAL SPECIFICATIONS (T_A = -40 to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications (T_A = −40 to +105°C)

R5F105xxGxx

Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G11 User's Manual.

Caution 3. Please contact Renesas Electronics sales office for derating of operation under T_A = +85 to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Caution 4. When operating temperature exceeds 85°C, only HS (high-speed main) mode can be used as the flash operation mode. Regulator mode should be used with the normal setting (MCSEL = 0).

Caution 5. The EV_{DD} pin is not present on products with 24 or less pins. Accordingly, replace EV_{DD} with V_{DD} and the voltage condition $1.6 \leq EV_{DD} \leq V_{DD} \leq 5.5$ V with $1.6 \leq V_{DD} \leq 5.5$ V.

Remark When the products “G: Industrial applications" is used in the range of T_A = -40 to +85°C, see **2. ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C)**.

3.4 AC Characteristics

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

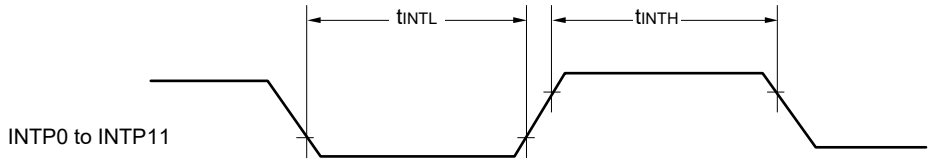
Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
		Subsystem clock (f_{SUB}) operation	f_{IL}	2.4 V ≤ V_{DD} ≤ 5.5 V		66.7		μs
		In the self-programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
External system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1		20	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1		16	MHz
External system clock input high-/low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
TI00 to TI03 input high-/low-level width	t_{TIH}, t_{TIL} Note 1				1/f_{MCK} + 10			ns
<R> TO00 to TO03, TKBO0, and TKBO1 output frequency Note 2	f_{TO}	TO00 to TO03, TKBO0, and TKBO1 (in the case of output from port pins other than P20)	HS (high-speed main) mode	4.0 V ≤ EV_{DD} ≤ 5.5 V			12	MHz
				2.7 V ≤ EV_{DD} < 4.0 V			8	
				2.4 V ≤ EV_{DD} < 2.7 V			4	
		TKBO1 (in the case of output from P20)	HS (high-speed main) mode	4.0 V ≤ V_{DD} ≤ 5.5 V			1.5	MHz
				2.7 V ≤ V_{DD} < 4.0 V			1.2	
				2.4 V ≤ V_{DD} < 2.7 V			1	
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode		4.0 V ≤ EV_{DD} ≤ 5.5 V			16	MHz
				2.7 V ≤ EV_{DD} < 4.0 V			8	
				2.4 V ≤ EV_{DD} < 2.7 V			4	
<R> Interrupt input high-/low-level width	t_{INTH}, t_{INTL}	INTP0 to INTP2, INTP9		2.4 V ≤ V_{DD} ≤ 5.5 V	1			μs
		INTP3 to INTP8, INTP10, INTP11		2.4 V ≤ EV_{DD} ≤ 5.5 V	1			
Key interrupt input low-level width	t_{KR}	KR0 to KR7		2.4 V ≤ EV_{DD} ≤ 5.5 V	250			ns
$\overline{RESET}$ low-level width	t_{RSL}				10			μs

Note 1. Following conditions must be satisfied on low level interface of EV_{DD} < V_{DD}.
2.4 V ≤ EV_{DD} ≤ 2.7 V: MIN.125 ns

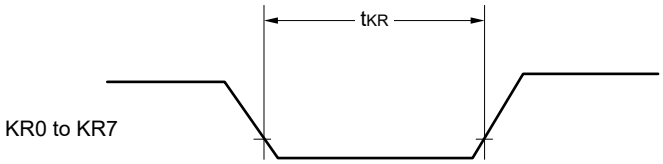
Note 2. When duty is 50%.

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3))

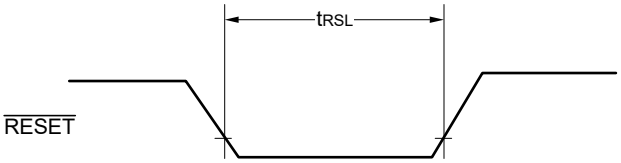
Interrupt Request Input Timing



Key Interrupt Input Timing



$\overline{\text{RESET}}$ Input Timing



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

When P01, P32, P53, P54 and P56 are used as SOmn pins

(T_A = -40 to +105°C, 2.7 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	2.7 V ≤ V_{DD} ≤ 5.5 V	250		ns
			2.4 V ≤ V_{DD} ≤ 5.5 V	500		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY1}/2 - 24		ns
		2.7 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY1}/2 - 36		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY1}/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ EV_{DD} ≤ 5.5 V		66		ns
		2.7 V ≤ EV_{DD} ≤ 5.5 V				ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		133		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}			38		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note 4			50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))

When P20 is used as SO10 pin

(T_A = -40 to +105°C, 2.7 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	2.7 V ≤ V_{DD} ≤ 5.5 V	1000		ns
			2.4 V ≤ V_{DD} ≤ 5.5 V	1200		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2 - 24		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 5.5 V		66		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		133		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}			38		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note 4			180	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
$\overline{SSI00}$ setup time	t_{SSIK}	DAPmn = 0	2.7 V ≤ V_{DD} ≤ 3.6 V	240		ns
			2.4 V ≤ V_{DD} < 2.7 V	400		ns
		DAPmn = 1	2.7 V ≤ V_{DD} ≤ 3.6 V	1/f_{MCK} + 240		ns
			2.4 V ≤ V_{DD} < 2.7 V	1/f_{MCK} + 400		ns
$\overline{SSI00}$ hold time	t_{KSSI}	DAPmn = 0	2.7 V ≤ V_{DD} ≤ 3.6 V	1/f_{MCK} + 240		ns
			2.4 V ≤ V_{DD} < 2.7 V	1/f_{MCK} + 400		ns
		DAPmn = 1	2.7 V ≤ V_{DD} ≤ 3.6 V	240		ns
			2.4 V ≤ V_{DD} < 2.7 V	400		ns

Caution **Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

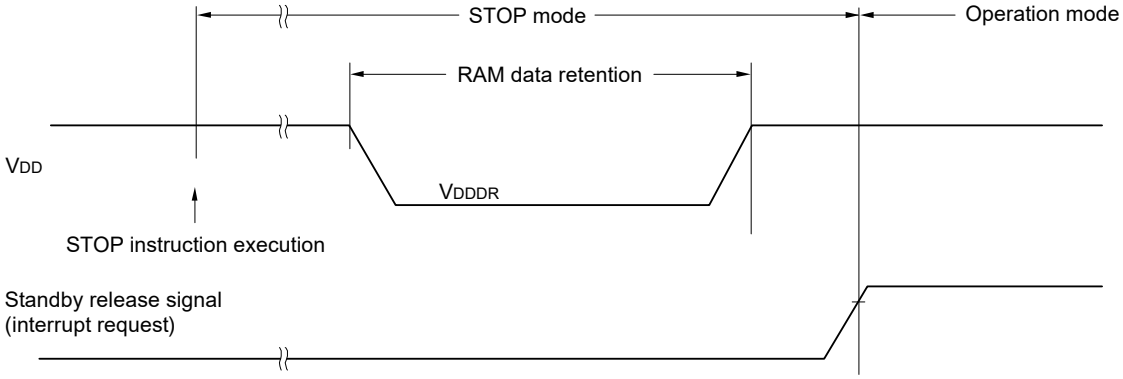
Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5, 12)

3.7 RAM Data Retention Characteristics

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44 Note		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



3.8 Flash Memory Programming Characteristics

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
System clock frequency	f_{CLK}			1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	C_{erwr}	Retained for 20 years	T_A = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year	T_A = 25°C		1,000,000		
		Retained for 5 years	T_A = 85°C	100,000			
		Retained for 20 years	T_A = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

Notice

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation or any other use of the circuits, software, and information in the design of your product or system. Renesas Electronics disclaims any and all liability for any losses and damages incurred by you or third parties arising from the use of these circuits, software, or information.
2. Renesas Electronics hereby expressly disclaims any warranties against and liability for infringement or any other claims involving patents, copyrights, or other intellectual property rights of third parties, by or arising from the use of Renesas Electronics products or technical information described in this document, including but not limited to, the product data, drawings, charts, programs, algorithms, and application examples.
3. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
4. You shall not alter, modify, copy, or reverse engineer any Renesas Electronics product, whether in whole or in part. Renesas Electronics disclaims any and all liability for any losses or damages incurred by you or third parties arising from such alteration, modification, copying or reverse engineering.
5. Renesas Electronics products are classified according to the following two quality grades: “Standard” and “High Quality”. The intended applications for each Renesas Electronics product depends on the product’s quality grade, as indicated below.

   "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; industrial robots; etc.

   "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control (traffic lights); large-scale communication equipment; key financial terminal systems; safety control equipment; etc.

   Unless expressly designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not intended or authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems; surgical implantations; etc.), or may cause serious property damage (space system; undersea repeaters; nuclear power control systems; aircraft control systems; key plant systems; military equipment; etc.). Renesas Electronics disclaims any and all liability for any damages or losses incurred by you or any third parties arising from the use of any Renesas Electronics product that is inconsistent with any Renesas Electronics data sheet, user’s manual or other Renesas Electronics document.
6. When using Renesas Electronics products, refer to the latest product information (data sheets, user’s manuals, application notes, “General Notes for Handling and Using Semiconductor Devices” in the reliability handbook, etc.), and ensure that usage conditions are within the ranges specified by Renesas Electronics with respect to maximum ratings, operating power supply voltage range, heat dissipation characteristics, installation, etc. Renesas Electronics disclaims any and all liability for any malfunctions, failure or accident arising out of the use of Renesas Electronics products outside of such specified ranges.
7. Although Renesas Electronics endeavors to improve the quality and reliability of Renesas Electronics products, semiconductor products have specific characteristics, such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Unless designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not subject to radiation resistance design. You are responsible for implementing safety measures to guard against the possibility of bodily injury, injury or damage caused by fire, and/or danger to the public in the event of a failure or malfunction of Renesas Electronics products, such as safety design for hardware and software, including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult and impractical, you are responsible for evaluating the safety of the final products or systems manufactured by you.
8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. You are responsible for carefully and sufficiently investigating applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive, and using Renesas Electronics products in compliance with all these applicable laws and regulations. Renesas Electronics disclaims any and all liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
9. Renesas Electronics products and technologies shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You shall comply with any applicable export control laws and regulations promulgated and administered by the governments of any countries asserting jurisdiction over the parties or transactions.
10. It is the responsibility of the buyer or distributor of Renesas Electronics products, or any other party who distributes, disposes of, or otherwise sells or transfers the product to a third party, to notify such third party in advance of the contents and conditions set forth in this document.
11. This document shall not be reprinted, reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products.

(Note 1) “Renesas Electronics” as used in this document means Renesas Electronics Corporation and also includes its directly or indirectly controlled subsidiaries.

(Note 2) “Renesas Electronics product(s)” means any product developed or manufactured by or for Renesas Electronics.

(Rev.4.0-1 November 2017)

RENESAS

SALES OFFICES

Renesas Electronics Corporation

http://www.renesas.com

Refer to "http://www.renesas.com/" for the latest and detailed information.

Renesas Electronics America Inc.
1001 Murphy Ranch Road, Milpitas, CA 95035, U.S.A.
Tel: +1-408-432-8888, Fax: +1-408-434-5351

Renesas Electronics Canada Limited
9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3
Tel: +1-905-237-2004

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
Room 1709 Quantum Plaza, No.27 ZhichunLu, Haidian District, Beijing, 100191 P. R. China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, 200333 P. R. China
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852 2886-9022

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics India Pvt. Ltd.
No.777C, 100 Feet Road, HAL 2nd Stage, Indiranagar, Bangalore 560 038, India
Tel: +91-80-67208700, Fax: +91-80-67208777

Renesas Electronics Korea Co., Ltd.
17F, KAMCO Yangjae Tower, 262, Gangnam-daero, Gangnam-gu, Seoul, 06265 Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5338

Colophon 7.0